

IN THE ABSTRACT:

Please replace the abstract of the invention with the following:

ABSTRACT

The invention relates to a process for etching at least one substrate, in particular at least one silicon wafer for the fabrication of DRAM memory chips. The process comprising at least one substrate, for a first etching step, is arranged for a predetermined time in a first vessel containing a first etchant, then at least one substrate, for a first rinsing step, is arranged for a predetermined time in a second vessel containing a first rinsing agent, the first rinsing agent containing at least one wetting agent, and then at least one substrate, for a second etching step, is arranged for a predetermined time in a third vessel containing a second etchant.